Vishay Siliconix

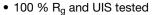
# Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.020			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.024			
I <sub>D</sub> (A) per leg	23			
Configuration	Dual			

# **FEATURES** TrenchFET® power MOSFET





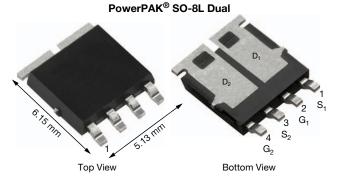


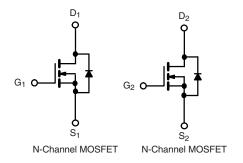
• Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





RoHS COMPLIANT HALOGEN **FREE** 





ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ952EP-T1-GE3

ABSOLUTE MAXIMUM RATING	S (T <sub>C</sub> = 25 °C, unles	s otherwise noted	d)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	60	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current	T <sub>C</sub> = 25 °C	1	23		
Continuous Drain Current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	13		
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	23	Α	
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	93		
Single Pulse Avalanche Current		I <sub>AS</sub>	21		
Single Pulse Avalanche Energy  L = 0.1 mH		E <sub>AS</sub>	22	mJ	
Maximum Davier Dissination 8	$T_C = 25 ^{\circ}C$	25	14/		
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	8.3	W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering Recommendations (Peak Temperature) c, d			260	C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount c	$R_{thJA}$	85	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	6	C/VV

- a. Pulse test; pulse width  $\leq 300 \, \mu s$ , duty cycle  $\leq 2 \, \%$ .
- b. When mounted on 1" square PCB (FR4 material).
- c. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static		•			I.	I.	l
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> :	= 0 V, I <sub>D</sub> = 250 μA	60	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$		1.5	2.0	2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μA
-		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10.3 A	-	0.012	0.020	
Drain-Source On-State Resistance a	Ь	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10.3 A, T <sub>J</sub> = 125 °C	-	-	0.030	Ω
Diani-Source Oil-State nesistance -	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> =10.3 A, T <sub>J</sub> = 175 °C	-	-	0.040	3.2
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 10.3 A	-	0.016	0.024	1
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> =	= 15 V, I <sub>D</sub> = 10.3 A	-	68	=.	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	1500	1800	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$	-	130	156	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	55	66	
Total Gate Charge <sup>c</sup>	Qg			-	24	30	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, I_D = 4.5 \text{ A}$	-	5	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	12		
Gate Resistance	$R_g$		f = 1 MHz	0.6	1.3	2.6	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	9	12	
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> :	= 30 V, $R_L = 30 \Omega$	-	6	8	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 1 \text{ A},$	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	25	30	ns
Fall Time <sup>c</sup>	t <sub>f</sub>	1		-	9	12	1
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	93	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	10.3 A, V <sub>GS</sub> = 0 V	-	0.7	1.1	V

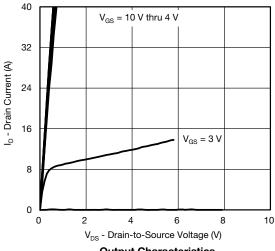
#### Notes

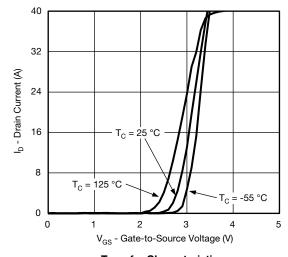
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



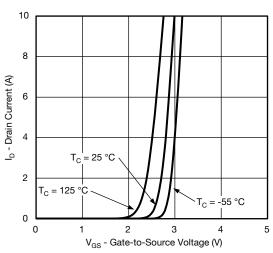
#### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

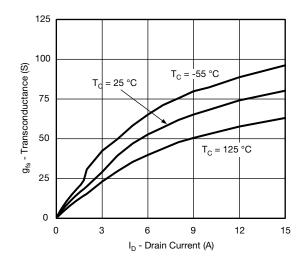




#### **Output Characteristics**

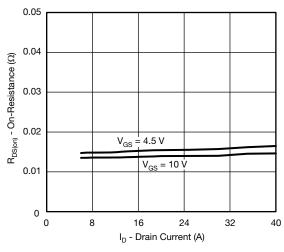


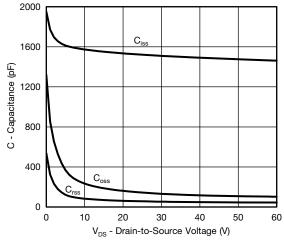




#### Transfer Characteristics

Transconductance



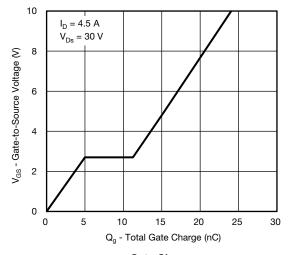


On-Resistance vs. Drain Current

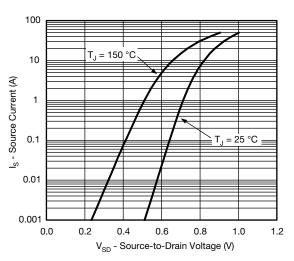
For technical questions, contact: automostechsu



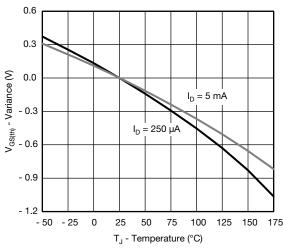
#### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



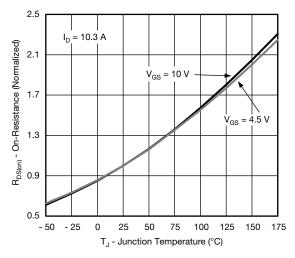
#### **Gate Charge**



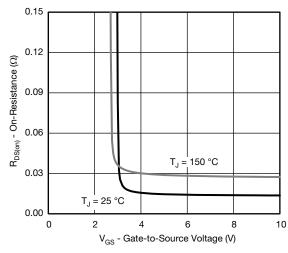
**Source Drain Diode Forward Voltage** 



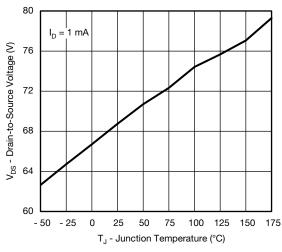
Threshold Voltage



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

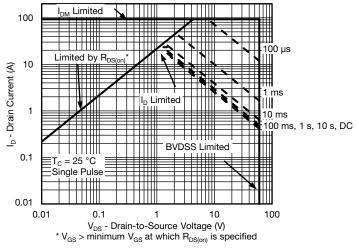


Drain Source Breakdown vs. Junction Temperature

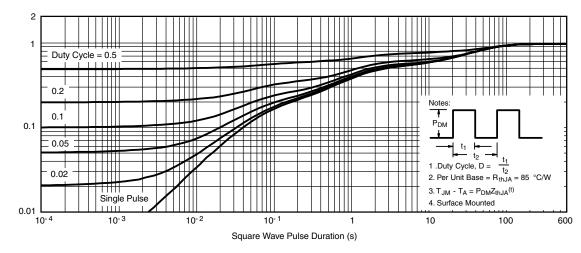


Normalized Effective Transient Thermal Impedance

#### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



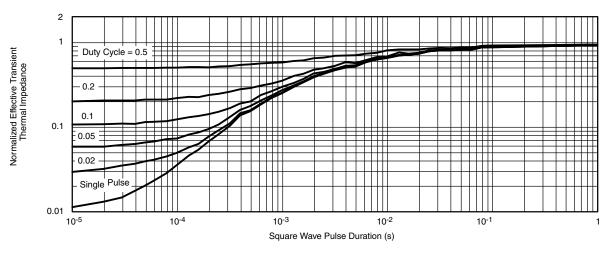
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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#### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

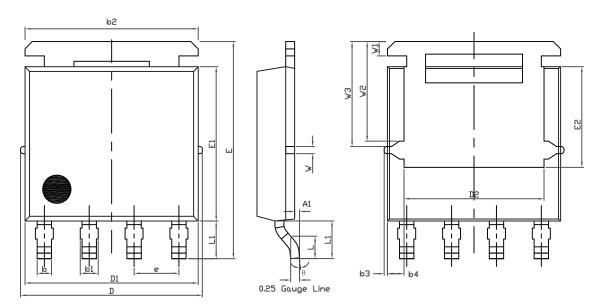
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

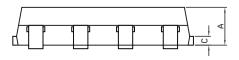
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?62862">www.vishay.com/ppg?62862</a>.

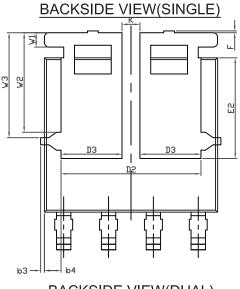
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# PowerPAK® SO-8L Case Outline for Al Parts



**TOPSIDE VIEW** 





BACKSIDE VIEW(DUAL)



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DIM		MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN. NOM.		MAX.		
Α	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094			0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC	•	0.050 BSC				
Е	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
K		0.51	•		0.020			
W		0.23		0.009				
W1	0.41		0.016					
W2		2.82		0.111				
W3		2.96			0.117			
q	0°	-	10°	0°	-	10°		

ECN: C15-1203-Rev. A, 07-Sep-15

DWG: 6044

#### Note

· Millimeters will gover



#### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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